

# ELI-NP Young Scientist and Young Engineer Days

• *January 10<sup>th</sup>-12<sup>th</sup>, 2022* •

*ELI-NP (IFIN-HH), Măgurele*

## TITLE:

**NANOMETER THIN DIAMOND-LIKE CARBON FILMS  
OPTIMIZED FOR LASER TARGETS FOR ELI-NP**

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- *doctoral research assist. (ELI-NP)* •
- *PhD stud. (UPB/SDIALA)* •

## OTHER TEAM MEMBERS

ELI-NP: *PhD Bogdan Diaconescu, PhD Cristina Gheorghiu, PhD stud. Cosmin Jalbă*

INFLPR: *PhD Bogdana Mitu, PhD Veronica Sătulu, PhD Valentina Mărăscu*

## LABORATORY SUPPORT

- *Target Laboratory from ELI-NP* •

- *Plasma Processes, Materials and Surfaces Group from INFLPR* •

- Motivation for laser-driven acceleration of carbon ions and protons using targets which consist in free-standing carbonic thin film
- Requirements for free-standing carbonic thin films for this application
- Suitability of diamond-like carbon
- Optimization of growth of diamond-like carbon thin films with required properties
- Characterization methods applied to check compatibility of grown films for free-standing target application
- Conclusions

# MOTIVATION

## Applications of irradiation with ACCELERATED C/H ions:

- testing of materials to ionizing radiation conditions.
- radiotherapy
  - due to high Linear Energy Transfer (LET) of high-energy ions/protons leading to high LET-dependent Relative Radiobiological Effectiveness (RBE). [1] [2]
- diagnostics and imagery. [3] [4] [5] [6]
- isotopes composition changing.
- generating of fluxes of neutrons and nuclei from secondary targets, subsequently usable.

**LASER-DRIVEN ACCELERATION of C/H ions  
from carbonic solid film targets  
(H from film impurities / residual composition)**

II  
V

**Fluxes of accelerated C/H ions  
much higher than classical accelerators**

[1] G. Milluzzo & D. Doria, et al., 'Dosimetry of laser-accelerated carbon ions for cell irradiation at ultra-high dose rate', Journal of Physics: Conference Series, vol. 1596, p. 012038, July 2020.

[2] D. Schardt, 'Tumor therapy with high-energy carbon ion beams', Nuclear Physics A 787 (2007) 633c–641c.

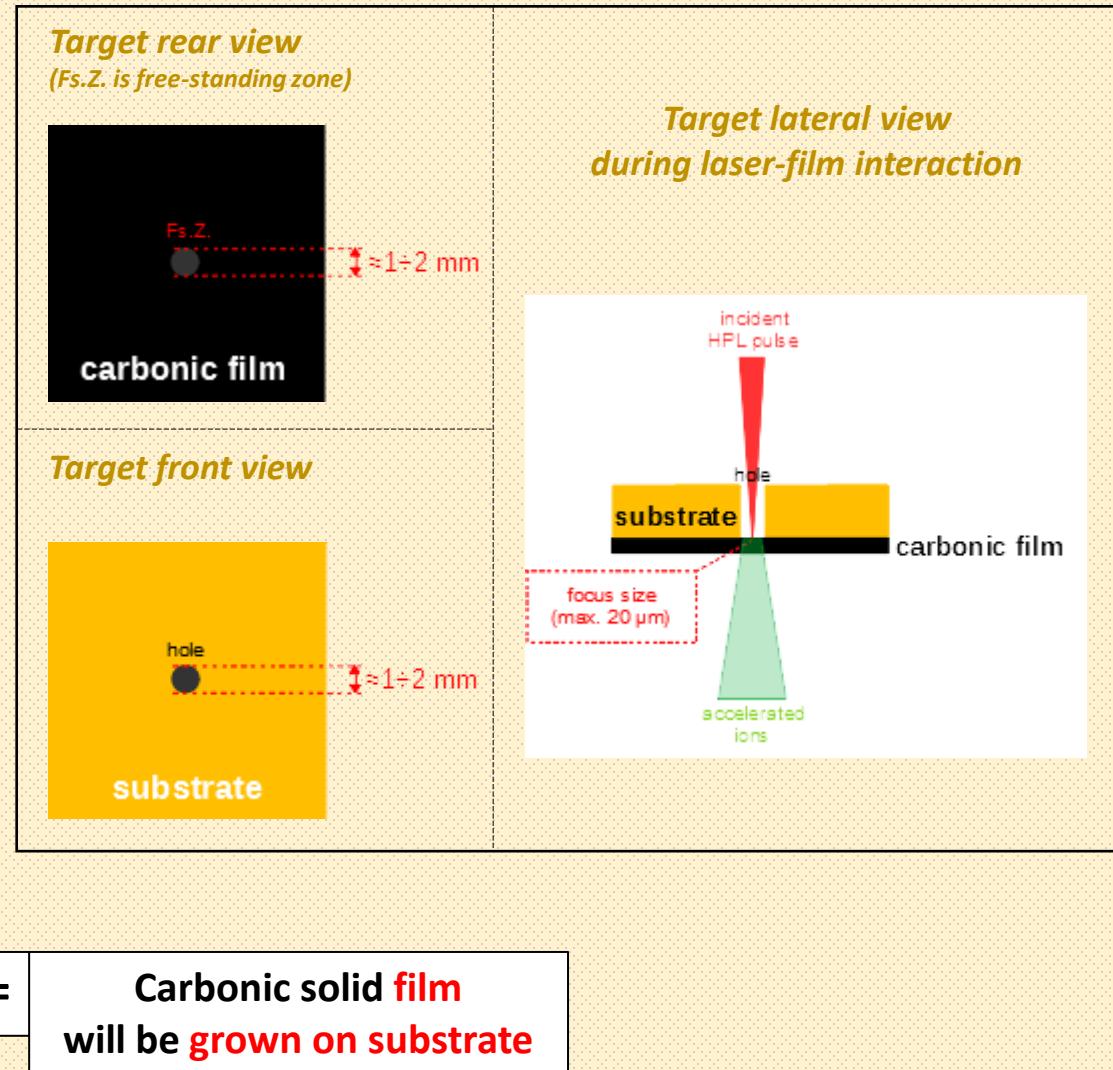
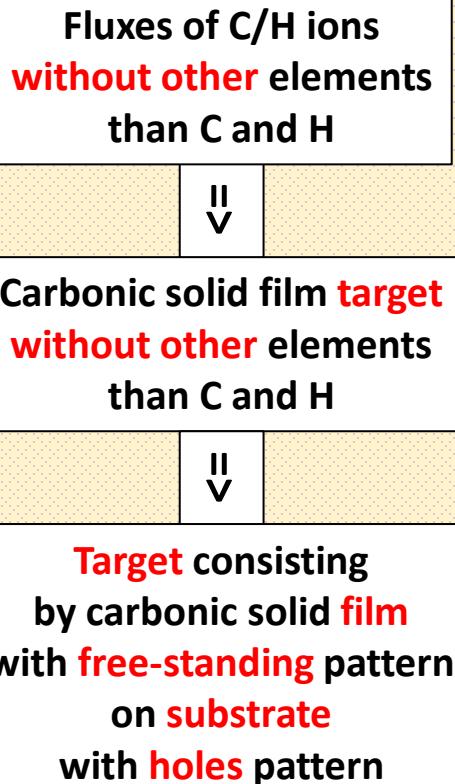
[3] M. Barberio, et al., 'Laser-Accelerated Proton Beams as Diagnostics for Cultural Heritage', Scientific Reports, 7:40415 (2017).

[4] H.-J. Ziock, et al., 'The proton radiography concept', LA-UR-98-1368, <http://lib-www.lanl.gov/la-pubs/00460235.pdf>.

[5] G. Poludniowski, et al., 'Proton radiography and tomography with application to proton therapy', BJR 2015, 88:105320150134.

[6] Lina Sheng, et al., 'Heavy-ion radiography facility at the Institute of Modern Physics', Laser and Particle Beams (2014), 32, 651-655.

# MOTIVATION



# REQUIREMENTS

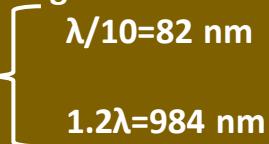
## THICKNESS of carbonic target:

- From **nanometers to micrometers** to accelerate **C and/or H ions** by **two main mechanisms or combination of these**:
  - **RPA (ultrathin/thin films)** which allows **highest kinetic energies** of **laser-driven** acceleration technique;
  - **TNSA (thin/thick films)** which has **less requirements** than **RPA** about **laser pulse** (duration, contrast, intensity), **advantageous** in applications which **don't need high kinetic energies**.

[7] [8] [9] [10] [11] [12]

## ROUGHNESS of carbonic target:

- **Below of  $\lambda/10$**  on surface zones which have sizes **higher** than laser spot diffraction limit  **$1.2\lambda$**

$\lambda=820$  nm for ELI-NP HPL pulses  $\Rightarrow$  

$$\left. \begin{array}{l} \lambda/10=82 \text{ nm} \\ 1.2\lambda=984 \text{ nm} \end{array} \right\}$$

## MECHANICAL STRENGTH of carbonic target:

- **High resistance** to mechanical tensile to avoid breaking by **target manipulation**, because of **high ratio aspect of free-standing zones**.

[7] D. Sangwan & D. Stutman & B. Diaconescu, et al., 'Simulations of carbon ion acceleration by 10 PW laser pulses on ELI-NP', *Laser and Particle Beams*, volume 37, issue 4, 2019, pp. 346-353.

[8] C. Scullion, D. Doria, et al., 'Polarization Dependence of Bulk Ion Acceleration from Ultrathin Foils Irradiated by High-Intensity Ultrashort Laser Pulses', *Phys. Rev. Lett.*, vol. 119, no. 5, p. 054801, 2017.

[9] Bulanov S. S., et al., 'Optimized laser pulse profile for efficient radiation pressure acceleration of ions', *Physics of Plasmas* 19 (2012) 093112.

[10] D. Jung, et al., 'Laser-driven 1 GeV carbon ions from preheated diamond targets in the break-out afterburner regime', *Physics of Plasmas*, vol. 20, p. 083103, 2013.

[11] B. M. Hegelich, et al., 'Laser-driven ion acceleration from relativistically transparent nanotargets', *New Journal of Physics*, vol. 15, p. 085015, 2013.

[12] D. Jung, et al., 'Efficient carbon ion beam generation from laser-driven volume acceleration', *New Journal of Physics*, vol. 15, p. 023007, 2013.

# DIAMOND-LIKE CARBON (DLC)

**Suitable carbonic materials** for such target films to C/H ions acceleration:

- Crystalline structures:
  - $sp^2$  hybridized C
    - **graphene**: film having **only ultrathin** thicknesses => **suitable only for some** acceleration mechanisms  
(if target doesn't contain a film from below carbonic materials, supplementary to graphene film)
  - $sp^3$  hybridized C:
    - **diamond**: film growth **requires very high** temperature/pressure for **one step** fabrication\*)
- Amorphous structures:
  - $sp^3$  and  $sp^2$  hybridized C:
    - **DLC**: film growth **can be** performed at **room/low** temperature in **vacuum** conditions for **one step** fabrication,\*)  
e.g. radio-frequency plasma-enhanced chemical vapor deposition (RF-PECVD)

\*) **one step** fabrication = **synthesis** and **film deposition** in **same time**

**DLC**:

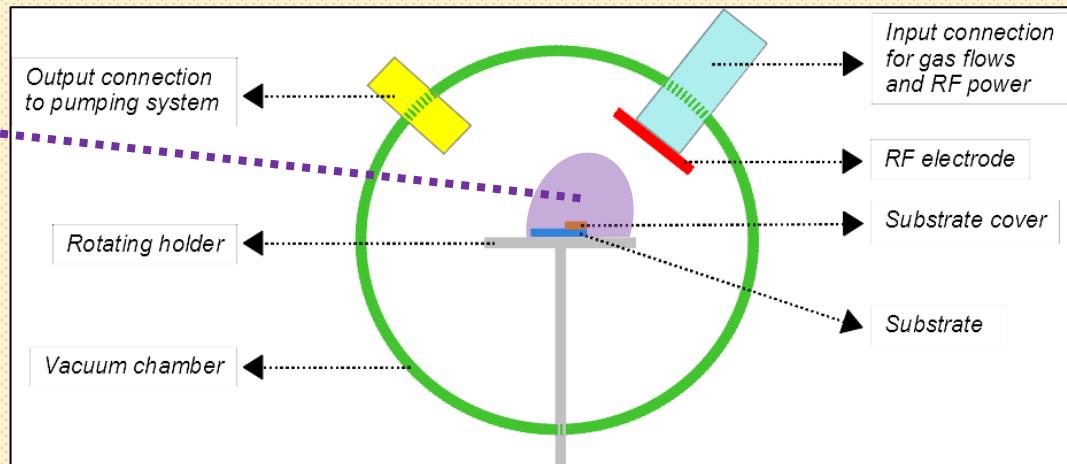
- DLC contains  $sp^3$  hybridized C in diamond (**cubic diamond**) and lonsdaleite (**hexagonal diamond**) local crystalline structures **without to form clearly separated crystallites** => DLC is **amorphous**
- **real** DLC contains  $sp^2$  hybridized C (*in graphite form*), **in addition** to  $sp^3$  C, because of **inherent imperfections** of **growth** processes => **mechanical** characteristics of DLC are **worsened** if graphite content is **too high**, **relative to** requirements of DLC **specific application** => **growth process optimization** to reduce  $sp^2$  C content

## DLC GROWTH

### RF plasma ions:

$[\text{CH}_3]^{n+}$ ,  $[\text{CH}_2]^{n+}$ ,  $[\text{CH}]^{n+}$ ,  $[\text{C}]^{n+}$ ,  
 $[\text{H}_2]^{+}$ ,  $[\text{H}]^{+}$ ,  $[\text{Ar}]^{n+}$

- Carbon from plasma constituents is deposited, forming  $\text{sp}^3$  &  $\text{sp}^2$  carbonic structures in film.
- Hydrogen more preferentially etches  $\text{sp}^3$  than  $\text{sp}^2$  carbon, from film.
- Globally,  $\text{sp}^3$  structures are favored to grow
- More hydrogen content in plasma leads to more  $\text{sp}^3\text{C}$  concentration in film (better DLC). [13]



DLC growth experimental set-up (RF-PECVD)

**substrate cover => portion of substrate uncoated by DLC => determination of DLC film thickness**

# DLC GROWTH

**Clean silicon wafers as substrates =>**

**=> Very smooth substrates =>**

**=> Worsening of DLC film roughnesses by substrates roughnesses is excluded =>**

**=> IF such worsening occurs, find of cause will focus on deposition process**

## METHOD 1

Precursor gas mixture	$\text{CH}_4 + \text{Ar}$	Total pressure	$\sim 10^{-3} \text{ mbar}$
C:H ratio	<b>1:4</b>	RF power	100 W
Gas flows	25 sccm $\text{CH}_4$ 50 sccm Ar	Deposition times	200 min ; 300 min

## METHOD 2

Precursor gas mixture	$\text{CH}_4 + \text{H}_2$	Total pressure	$\sim 1.5 \times 10^{-3} \text{ mbar}$
C:H ratio	<b>1:9 (increased H content)</b>	RF power	100 W
Gas flows	25.0 sccm $\text{CH}_4$ 62.5 sccm $\text{H}_2$	Deposition times	23 min ; 34 min ; 45 min ; 60 min

# DLC GROWTH

$$X_{MN} = \frac{K_M}{K_M + K_N}$$

Where  $K_M$  and  $K_N$  are concentration of M, respectively N, chemical element from gas precursor mixture

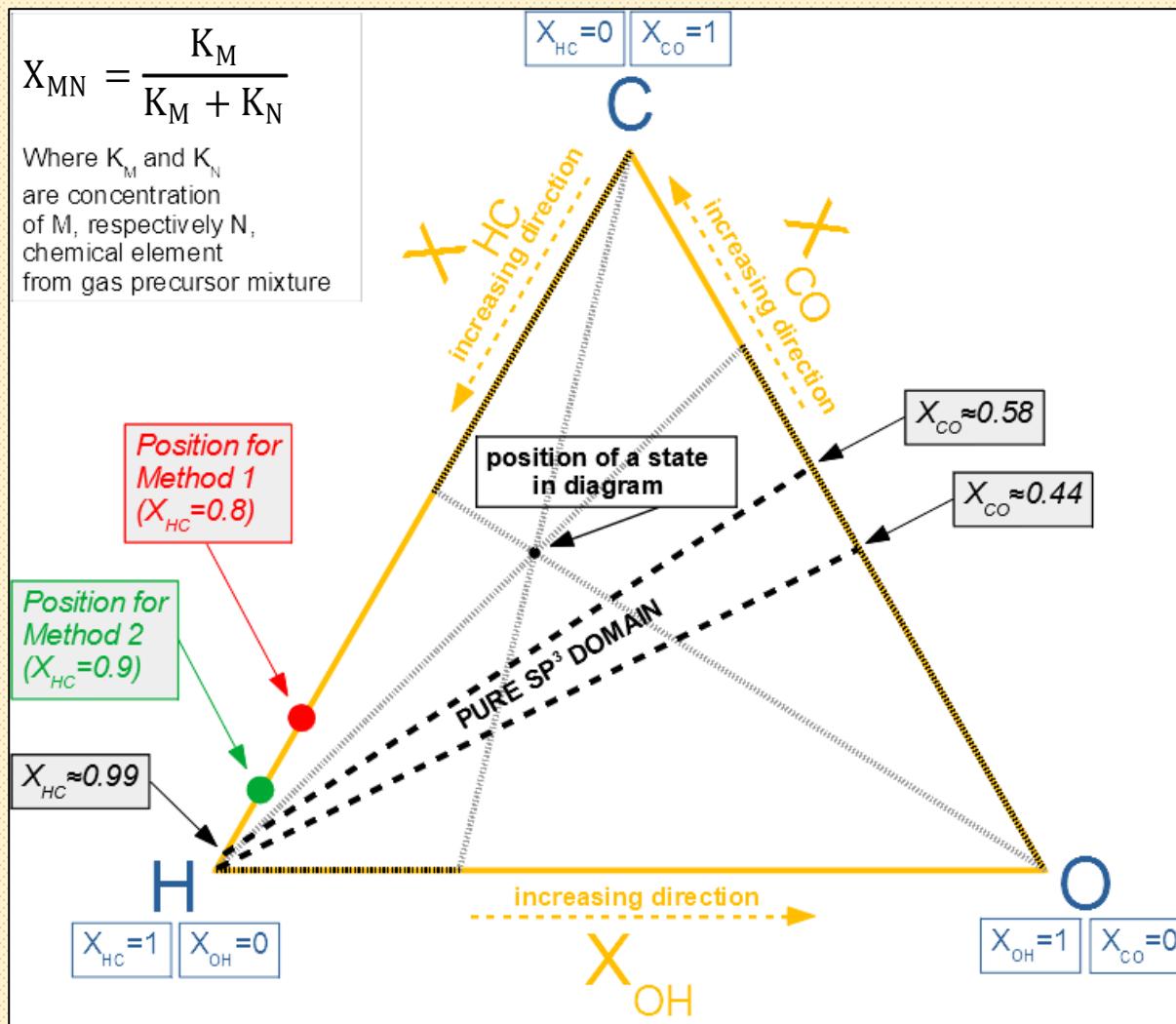
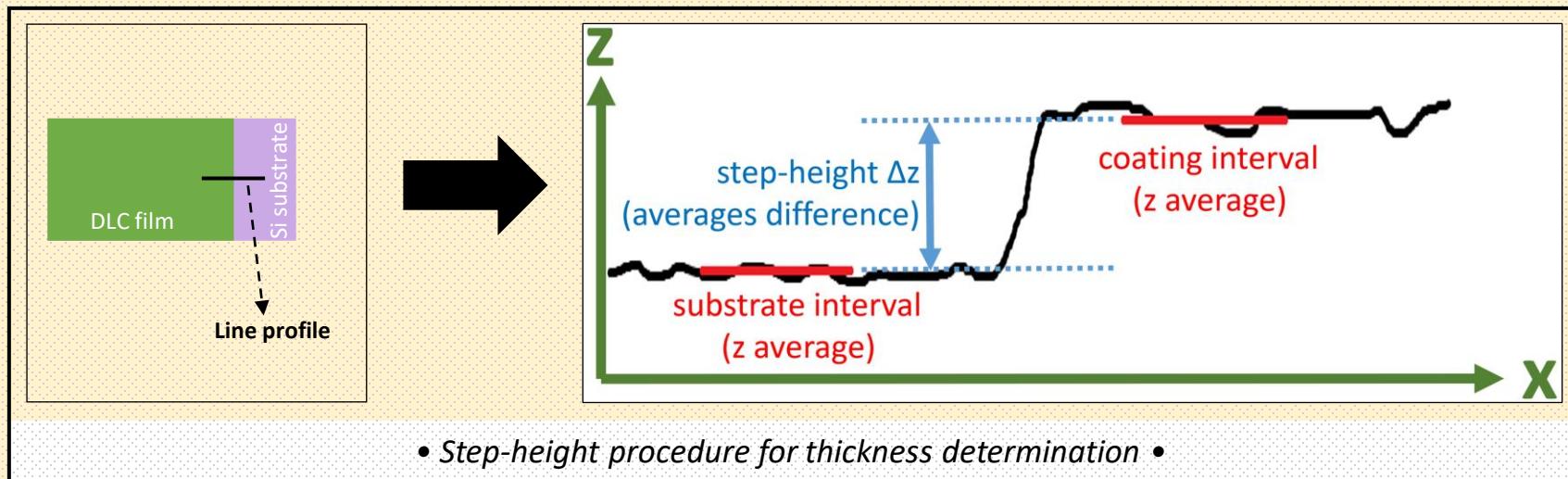


Diagram of pure  $sp^3$  deposited carbonic films, related to C/H/O-composition of precursor gas mixture, for CVD processes [13]

# DLC CHARACTERIZATION

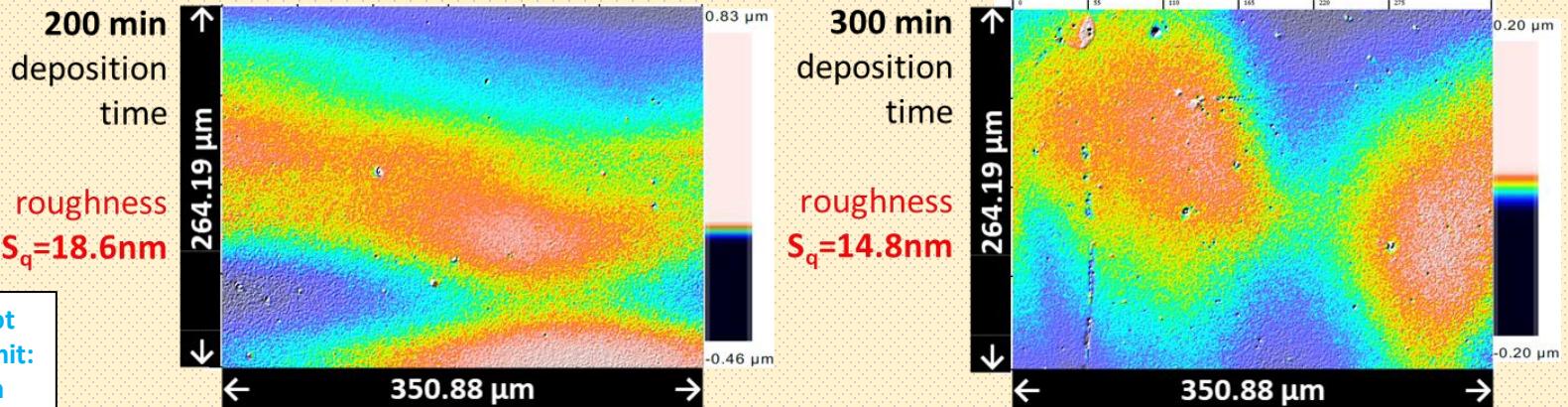
## CONTACT (MECHANICAL) PROFILOMETRY



METHOD 1 SAMPLES			METHOD 2 SAMPLES				
Deposition time $\Delta t$ [min]	200	300	Deposition time [min]	23	34	45	60
Thickness $\Delta z$ [nm]	381.7	535.5	Thickness [nm]	21.8	26.3	50.6	57.0
$\Delta z(\Delta t)$ linear fit					$\Delta z(\Delta t)$ linear fit		
Deposition rate (slope)					Deposition rate (slope)		
1.8 nm/min					1.0 nm/min		

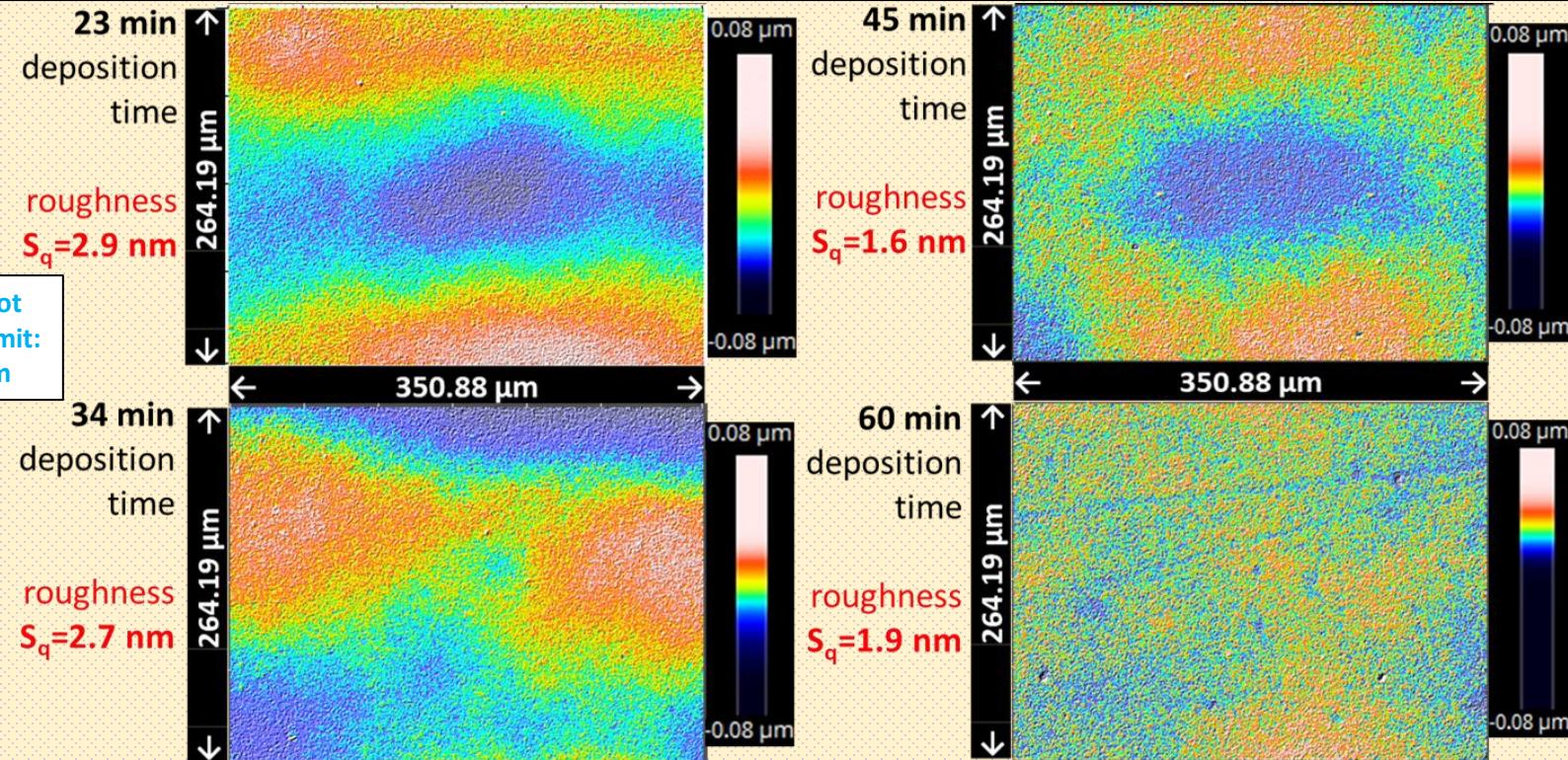
# DLC CHARACTERIZATION

## METHOD 1 samples



OPTICAL PROFILOMETRY → Roughness determination → Placement under of  $\lambda/10=82\text{ nm}$

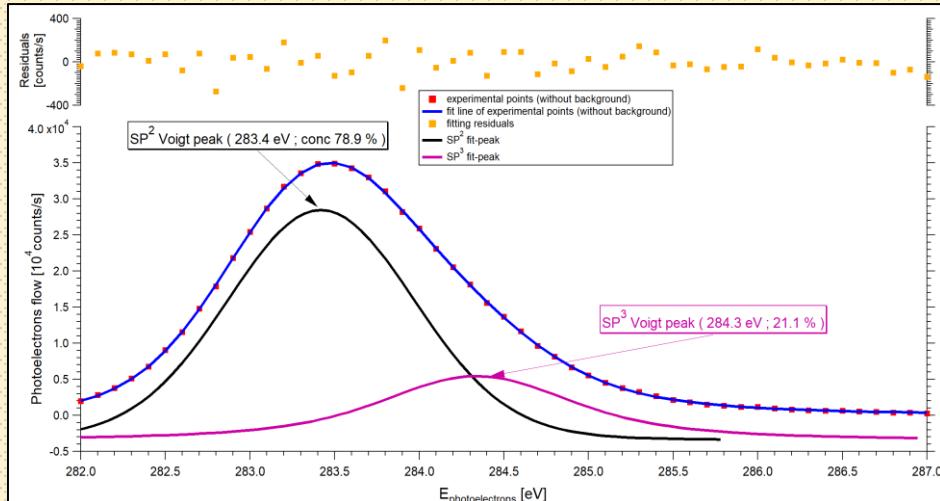
## METHOD 2 samples



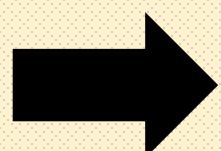
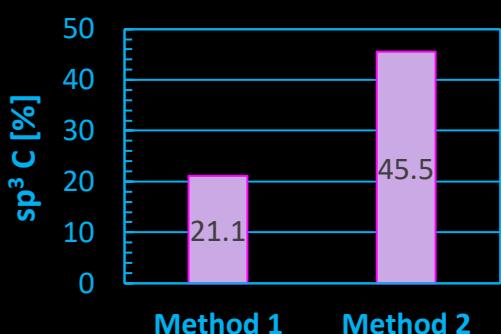
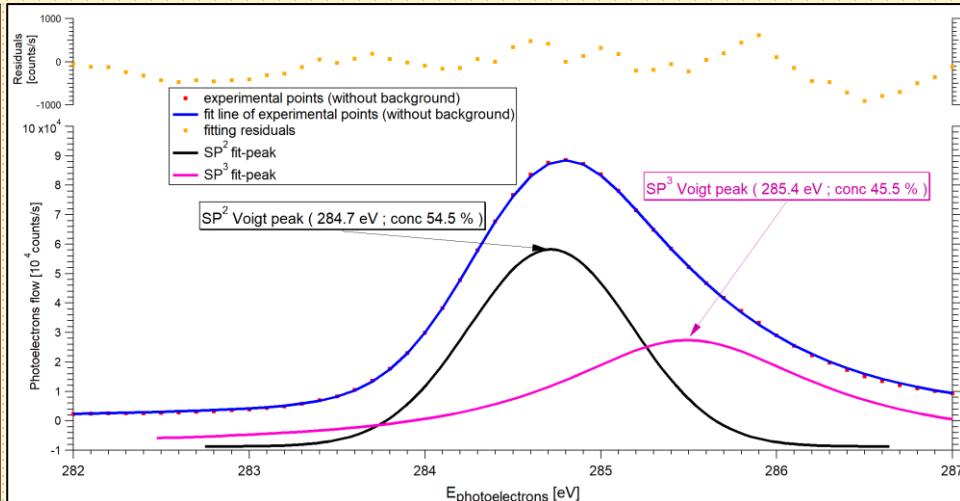
# DLC CHARACTERIZATION

## X-RAY PHOTOEMISSION SPECTROMETRY (XPS)

DLC film from **method 1** deposition  
(XPS spectra of C-C bonds)



DLC film from **method 2** deposition  
(XPS spectra of C-C bonds)



Improving of DLC film **mechanical strength**  
by **method 2**, comparing to **method 1**

## CONCLUSIONS

### CONCLUSION

*Characterization data shows compliance of grown DLC films with HPL target requirements:*

- $\lambda/10$  limit of roughnesses on large area ( $\approx 92700 \mu\text{m}^2$ )
- $sp^3$  C content assures mechanical strength for application concerned

### NEXT STEPS

- *Implementation of developed growth method on copper substrates (much cheaper than silicon wafers)*
- *Patterned etching of copper substrates to achieve free-standing zones of deposited DLC film*
- *HPL acceleration of carbon & hydrogen ions using DLC targets*

**THANK YOU  
FOR ATTENTION**

**!!!**